

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

NEC

The μ PA1874B is a switching device, which can be driven directly by a 2.5 V power source.

The μ PA1874B features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- · Low on-state resistance
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1874BGR-9JG	Power TSSOP8

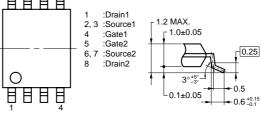
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

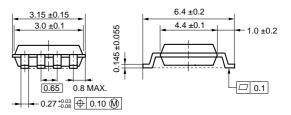
Drain to Source Voltage (VGs = 0 V)	VDSS	30.0	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±12.0	V
Drain Current (DC) ^{Note 1}	ID(DC)	±8.0	А
Drain Current (pulse) Note 2	D(pulse)	±80.0	А
Total Power Dissipation Note 1	Pτ	2.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C
	-		

Notes 1. Mounted on ceramic board of 50 $\text{cm}^2 \times 1.1 \text{ mm}$

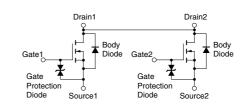
2. PW \leq 10 μ s, Duty Cycle \leq 1%

PACKAGE DRAWING (Unit: mm)





EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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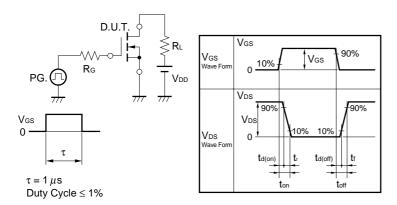
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30.0 V, V _{GS} = 0 V			1.0	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 12.0 V, V_{DS} = 0 V$			±10.0	μA
Gate Cut-off Voltage	V _{GS(off)}	V_{DS} = 10.0 V, I_D = 1.0 mA	0.50	1.00	1.50	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10.0 V, I _D = 4.0 A	5			S
Drain to Source On-state Resistance Note	RDS(on)1	V_{GS} = 4.5 V, I _D = 4.0 A	9.0	11.5	14.0	mΩ
	RDS(on)2	V_{GS} = 4.0 V, I _D = 4.0 A	9.5	12.0	14.5	mΩ
	RDS(on)3	Vgs = 3.1 V, Id = 4.0 A	10.0	13.0	16.5	mΩ
	RDS(on)4	V_{GS} = 2.5 V, I_D = 4.0 A	11.0	15.0	19.5	mΩ
Input Capacitance	Ciss	V _{DS} = 10.0 V		930		pF
Output Capacitance	Coss	V _{GS} = 0 V		170		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		120		pF
Turn-on Delay Time	td(on)	V _{DD} = 10.0 V, I _D = 4.0 A		46		ns
Rise Time	tr	V _{GS} = 4.0 V		230		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		260		ns
Fall Time	tr			250		ns
Total Gate Charge	QG	V _{DD} = 24.0 V		10.0		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 4.0 V		2.0		nC
Gate to Drain Charge	Qgd	ID = 8.0 A		4.5		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 8.0 A, VGS = 0 V		0.82		V
Reverse Recovery Time	trr	IF = 8.0 A, VGS = 0 V		150		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/ <i>µ</i> s		80		nC

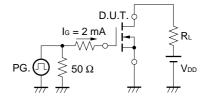
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Note Pulsed: PW $\leq 350~\mu s,$ Duty Cycle $\leq 2\%$

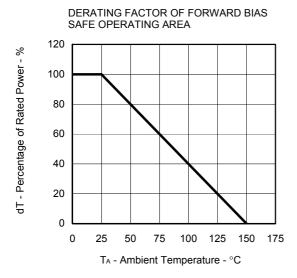
TEST CIRCUIT 1 SWITCHING TIME



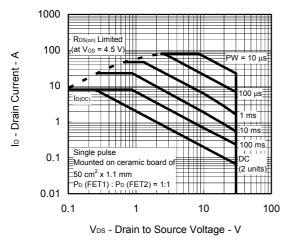
TEST CIRCUIT 2 GATE CHARGE

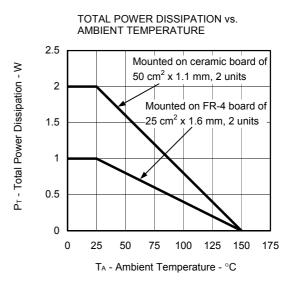


TYPICAL CHARACTERISTICS (TA = 25°C)

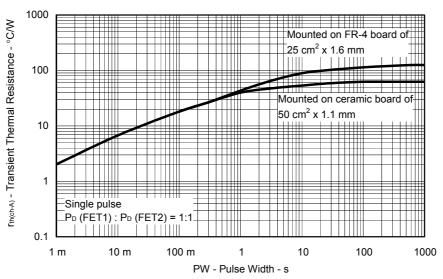




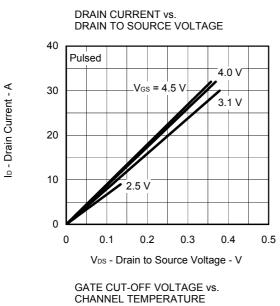


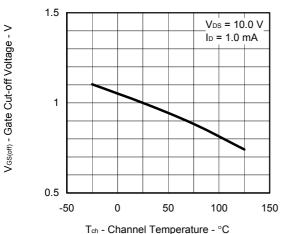


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

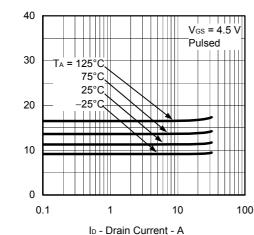


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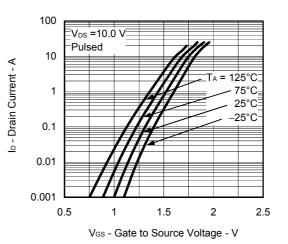




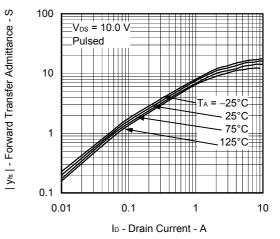
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



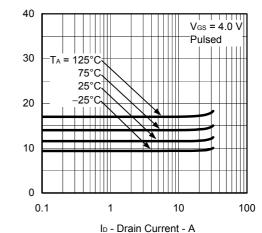
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

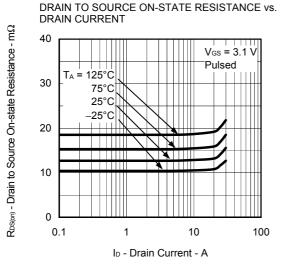


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

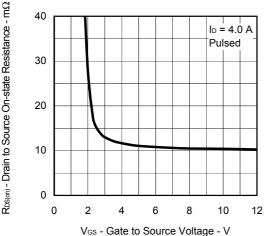


 $R_{DS(cn)}$ - Drain to Source On-state Resistance - $m\Omega$

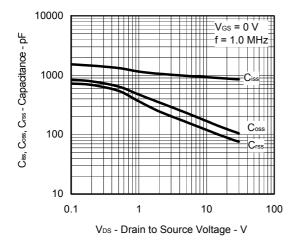
 $R_{DS(m)}$ - Drain to Source On-state Resistance - m Ω



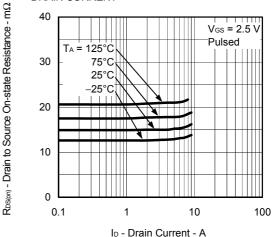




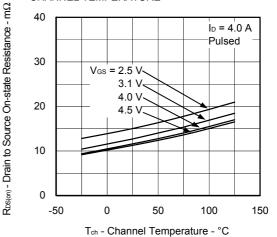
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



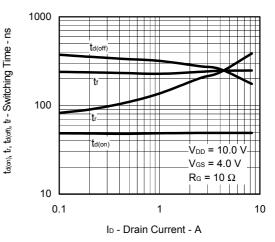
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



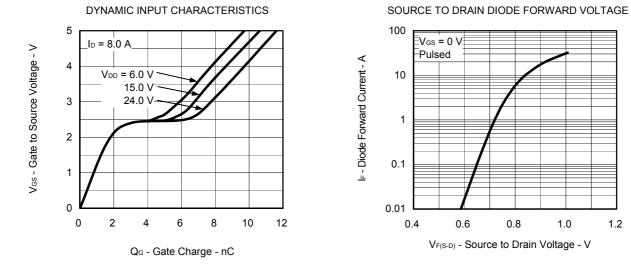
SWITCHING CHARACTERISTICS



1.0

1.2





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